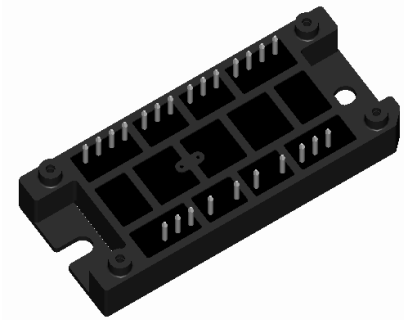
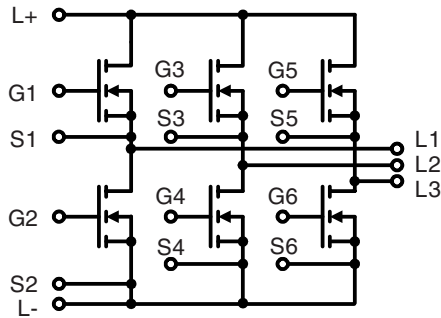


Three phase full bridge with Trench MOSFETs

$$V_{DSS} = 100 \text{ V}$$

$$R_{DSon} = 3.6 \text{ m}\Omega$$

$$I_{D25} = 210 \text{ A}$$



MOSFETs		
Symbol	Conditions	Maximum Ratings
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	100 V
V_{GS}		± 20 V
I_{D25}	$T_C = 25^\circ\text{C}$	210 A
I_{D80}	$T_C = 80^\circ\text{C}$	170 A
I_{D25}	$T_C = 25^\circ\text{C}$ (diode)	210 A
I_{D80}	$T_C = 80^\circ\text{C}$ (diode)	170 A

Applications

AC drives

- in automobiles and trucks
 - electric power steering
 - starter generator
 - etc...

- in industrial vehicles
 - propulsion drives
 - fork lift drives

- in battery supplied equipment

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
R_{DSon}	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ A}$		3.6	5.2 m Ω
V_{GSth}	$V_{DS} = 20 \text{ V}; I_D = 2 \text{ mA}$	2		4 V
I_{DSS}	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.25	0.02 mA mA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2 μA
Q_g	$V_{GS} = 10 \text{ V}; V_{DS} = 80 \text{ V}; I_D = 200 \text{ A}$		430	nC
Q_{gs}			90	nC
Q_{gd}			180	nC
$t_{d(on)}$	$V_{GS} = 10 \text{ V}; V_{DS} = 50 \text{ V};$ $I_D = 50 \text{ A}; R_G = 2.7 \Omega$		40	ns
t_r			100	ns
$t_{d(off)}$			260	ns
t_f			100	ns
V_F	(diode) $I_F = 100 \text{ A}; V_{GS} = 0 \text{ V}$		1.0	1.5 V
t_{rr}	(diode) $I_F = 40 \text{ A}; -di/dt = 200 \text{ A}/\mu\text{s}; V_{DS} = 30 \text{ V}$		100	ns
R_{thJC}	with heat transfer paste			0.26 K/W
R_{thJH}			0.51	K/W

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - solder terminals for PCB mounting
 - isolated DCB ceramic base plate with optimized heat transfer

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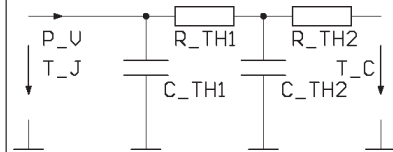
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Module

Symbol	Conditions	Maximum Ratings
T_{VJ}		-40...+175 °C
T_{stg}		-40...+125 °C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}; t = 1 \text{ min}$	500 V~
M_d	Mounting torque (M5)	2 - 2.5 Nm

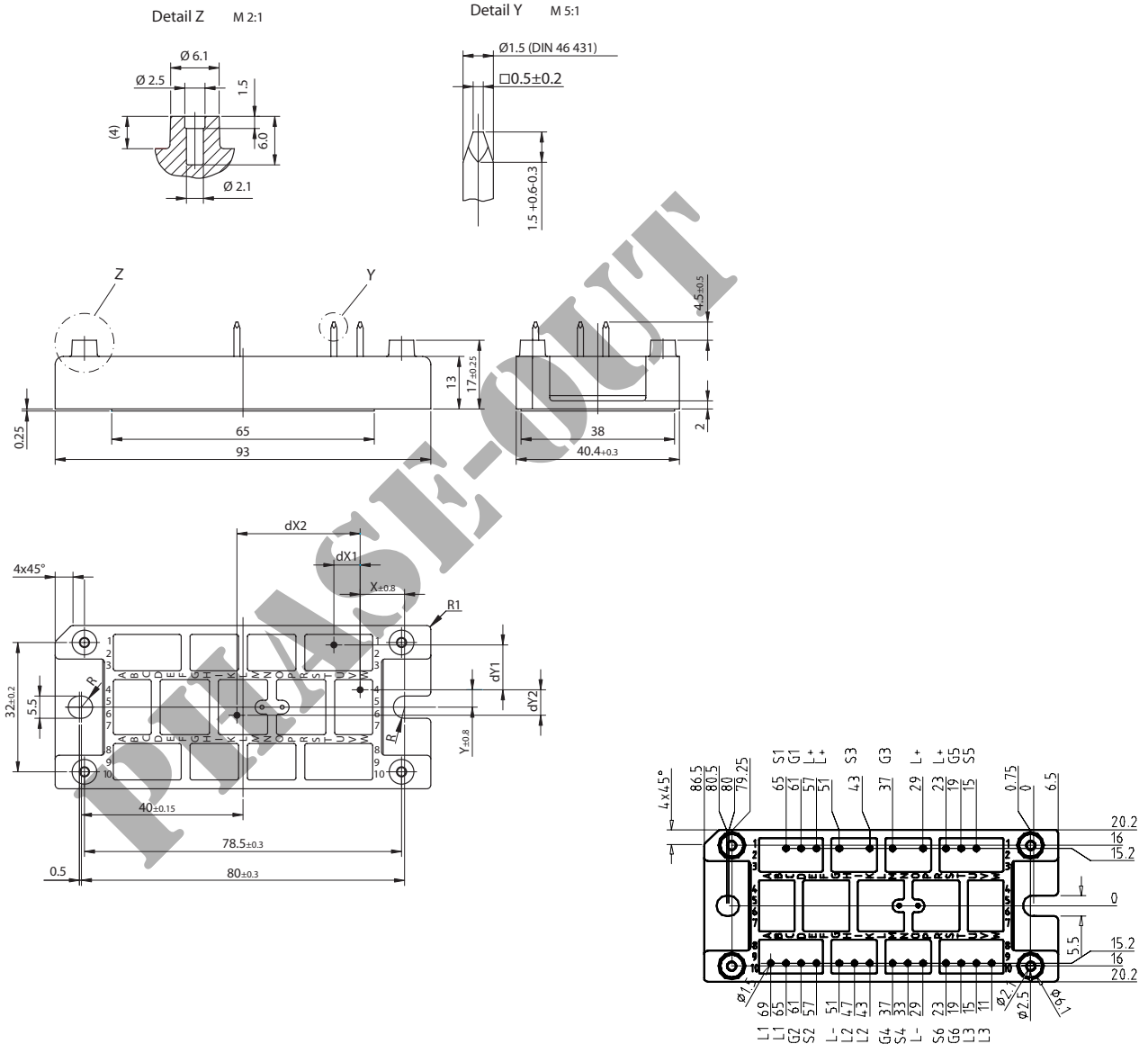
Symbol	Conditions	Characteristic Values		
		$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
Weight	typ.		80	g

Equivalent Circuits for Simulation
Thermal Response


junction - case (typ.)

$$C_{th1} = 0.13 \text{ J/K}; R_{th1} = 0.08 \text{ K/W}$$

$$C_{th2} = 0.22 \text{ J/K}; R_{th2} = 0.18 \text{ K/W}$$

Dimensions in mm (1 mm = 0.0394")


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